CD54/74HC30, CD54/74HCT30

Data sheet acquired from Harris Semiconductor SCHS121A

August 1997 - Revised May 2000

High Speed CMOS Logic 8-Input NAND Gate

Features

- · Buffered Inputs
- Typical Propagation Delay: 10ns at V_{CC} = 5V, C_L = 15pF, T_A = 25°C
- Fanout (Over Temperature Range)
- Wide Operating Temperature Range ... -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility,
 V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
 - CMOS Input Compatibility, I_I \leq 1 μ A at V_{OL}, V_{OH}

Description

The 'HC30 and 'HCT30 each contain an 8-input NAND gate in one package. They provide the system designer with the direct implementation of the positive logic 8-input NAND function. Logic gates utilize silicon gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The HCT logic family is functionally pin compatible with the standard LS logic family.

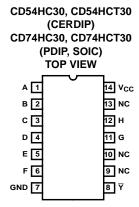
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC30F	-55 to 125	14 Ld CERDIP
CD54HC30F3A	-55 to 125	14 Ld CERDIP
CD74HC30E	-55 to 125	14 Ld PDIP
CD74HC30M	-55 to 125	14 Ld SOIC
CD54HCT30F3A	-55 to 125	14 Ld CERDIP
CD54HCT30H	-55 to 125	Die
CD74HCT30E	-55 to 125	14 Ld PDIP
CD74HCT30M	-55 to 125	14 Ld SOIC

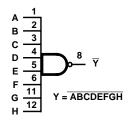
NOTES:

- 1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
- Die for this part number is available which meets all electrical specifications. Please contact your local TI sales office or customer service for ordering information.

Pinout



Functional Diagram

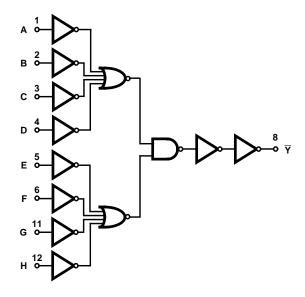


TRUTH TABLE

INPUTS											
Α	В	С	D	E	F	G	Н	OUTPUT			
L	Х	Х	Х	Х	Х	Х	Х	Н			
Х	L	Х	Х	Х	Х	Х	Х	Н			
Х	Х	L	Х	Х	Х	Х	Х	Н			
Х	Х	Х	L	Х	Х	Х	Х	Н			
Х	Х	Х	Х	L	Х	Х	Х	Н			
Х	Х	Х	Х	Х	L	Х	Х	Н			
Х	Х	Х	Х	Х	Х	L	Х	Н			
Х	Х	Х	Х	Х	Х	Х	L	Н			
Н	Н	Н	Н	Н	Н	Н	Н	L			

NOTE: H = HIGH Voltage Level, L = LOW Voltage Level, X = Irrelevant

Logic Symbol



CD54/74HC30, CD54/74HCT30

Absolute Maximum Ratings

DC Supply Voltage, V _{CC} 0.5V to 7V
DC Input Diode Current, I _{IK}
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$
DC Output Diode Current, I _{OK}
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$
DC Output Source or Sink Current per Output Pin, IO
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$
DC V_{CC} or Ground Current, I_{CC} or I_{GND}

Thermal Information

Thermal Resistance (Typical, Note 3)	θ _{JA} (°C/W)	θ_{JC} ($^{\circ}C/W$)
PDIP Package	100	N/A
CERDIP Package	130	55
SOIC Package	180	N/A
Maximum Junction Temperature (Hermetic	Package or Di	e) 175 ⁰ C
Maximum Junction Temperature (Plastic F	Package)	150 ^o C
Maximum Storage Temperature Range	65	^o C to 150°C
Maximum Lead Temperature (Soldering 1	0s)	300°C
(SOIC - Lead Tips Only)		

Operating Conditions

Temperature Range (T _A)55°C to 125°C
Supply Voltage Range, V _{CC}
HC Types2V to 6V
HCT Types
DC Input or Output Voltage, V _I , V _O 0V to V _{CC}
Input Rise and Fall Time
2V
4.5V 500ns (Max)
6V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. $\theta_{\mbox{\scriptsize JA}}$ is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

			ST ITIONS	•		25°C			O +85°C	-55°C TO 125°C		
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES												
High Level Input	V _{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
Voltage				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
Voltage				4.5	ı	-	1.35	-	1.35	-	1.35	V
				6	i	-	1.8	-	1.8	i	1.8	V
High Level Output	Voн	V _{IH} or V _{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
Voltage CMOS Loads			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output			-	-	ı	-	-	-	-	ı	-	V
Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output	V _{OL}	V _{IH} or	0.02	2	ı	-	0.1	-	0.1	ı	0.1	V
Voltage CMOS Loads		V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	i	-	0.1	-	0.1	i	0.1	V
Low Level Output			-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	lı	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μА

CD54/74HC30, CD54/74HCT30

DC Electrical Specifications (Continued)

			TEST CONDITIONS		25°C			-40°C T	O +85°C	-55°C TO 125°C		
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Quiescent Device Current	Icc	V _{CC} or GND	0	6	-	-	2	-	20	-	40	μА
HCT TYPES	•											
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	-0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	II	V _{CC} and GND	-	5.5	-		±0.1	-	±1	-	±1	μА
Quiescent Device Current	Icc	V _{CC} or GND	0	5.5	-	-	2	-	20	-	40	μА
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	Δl _{CC}	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μΑ

NOTE:

HCT Input Loading Table

INPUT	UNIT LOADS
All	0.6

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g. $360\mu A$ max at $25^{\circ}C$.

Switching Specifications Input t_r , t_f = 6ns

		TEST	TEST	TEST	v _{cc}		25°C		-40°C T	O 85°C	-55°C T	O 125°C	
PARAMETER	SYMBOL	CONDITIONS	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS		
HC TYPES													
Propagation Delay, Input to	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	130	-	165	-	195	ns		
Output (Figure 1)			4.5	-	-	26	-	33	-	39	ns		
			6	-	-	22	-	28	-	33	ns		
Propagation Delay, Data Input to Output Y	t _{PLH} , t _{PHL}	C _L = 15pF	5	-	10	-	-	-	-	-	ns		

^{4.} For dual-supply systems theoretical worst case ($V_I = 2.4V$, $V_{CC} = 5.5V$) specification is 1.8mA.

CD54/74HC30, CD54/74HCT30

Switching Specifications Input t_r , $t_f = 6ns$ (Continued)

		TEST V _{CC}		25°C			-40°C T	O 85°C	-55°C TO 125°C		
PARAMETER	SYMBOL	CONDITIONS	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Transition Times (Figure 1)	t _{TLH} , t _{THL}	C _L = 50pF	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	Cl	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 5, 6)	C _{PD}	-	5	-	25	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay, Input to Output (Figure 2)	t _{RHL} , t _{PHL}	C _L = 50pF	4.5	-	-	28	-	35	-	42	ns
Propagation Delay, Data Input to Output Y	t _{PLH} , t _{PHL}	C _L = 15pF	5	-	11	-	-	-	-	-	ns
Transition Times (Figure 2)	t _{TLH} , t _{THL}	C _L = 50pF	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C _I	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 5, 6)	C _{PD}	-	5	-	26	-	-	-	-	-	pF

NOTES:

- 5. C_{PD} is used to determine the dynamic power consumption, per gate.
- 6. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

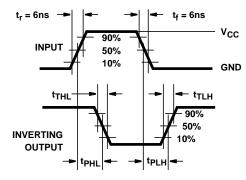


FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGA-TION DELAY TIMES, COMBINATION LOGIC

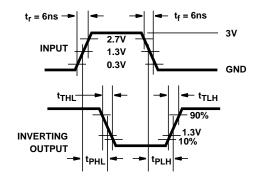


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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